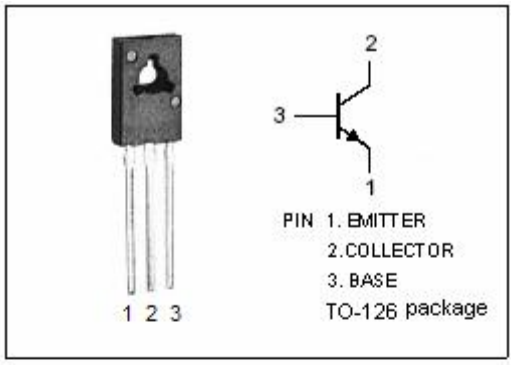
isc Silicon NPN Power Transistor BD232

DESCRIPTION

- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 300V(Min)



APPLICATIONS

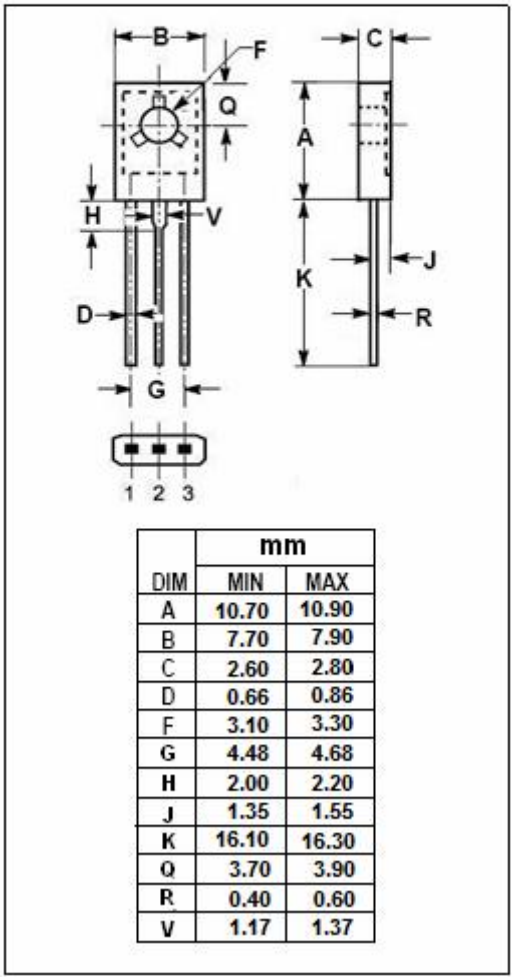
- Designed for use in power output stages and line driver in TV receivers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current-Continuous	0.5	A
I_B	Base Current-Continuous	0.25	A
P_C	Collector Power Dissipation @T_C=25℃	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	6.25	℃/W



DIM	mm MIN	MAX
A	10.70	10.90
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	16.10	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA; I_B= 0	300			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 150mA; I_B= 15mA			1.0	V
I_{CES}	Collector Cutoff Current	V_{CE}= 500V; V_{BE}= 0			100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			10	μA
h_{FE-1}	DC Current Cain	I_C= 50mA ; V_{CE}= 5V	25		150	
h_{FE-2}	DC Current Cain	I_C= 150mA ; V_{CE}= 5V	20			